

SANYO	No.550F	2SD879
		NPN Epitaxial Planar Silicon Transistor
1.5V, 3V Strobe Applications		

Applications

- In applications where two NiCd batteries are used to provide 2.4V, two 2SD879s are used.
- The charge time is approximately 1 second faster than that of germanium transistors.
- Less power dissipation because of low Collector-to-Emitter Voltage $V_{CE(sat)}$, permitting more flashes of light to be emitted.
- Small package and large allowable collector dissipation (TO-92, PC = 750mW).
- Large current capacity and highly resistant to breakdown.
- Excellent linearity of h_{FE} in the region from low current to high current.

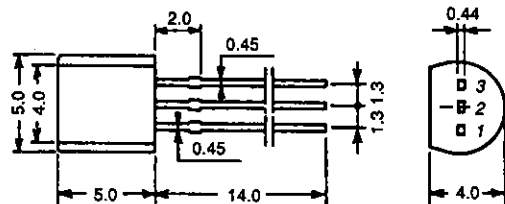
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	30	V
Collector-to-Emitter Voltage	V_{CEX}	20	V
Collector-to-Emitter Voltage	V_{CEO}	10	V
Emitter-to-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	3	A
Collector Current (Pulse)	I_{CP}	5	A
Collector Dissipation	P_C	750	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

		min	typ	max	unit
Collector Cutoff Current	I_{CBO}			1.0	μA
Emitter Cutoff Current	I_{EBO}			1.0	μA
DC Current Gain	h_{FE}	140	210		
Gain-Bandwidth Product	f_T		200		MHz
Output Capacitance	C_{ob}		30		pF
C-E Saturation Voltage	$V_{CE(sat)}$		0.3	0.4	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	30			V
C-E Breakdown Voltage	$V_{(BR)CEX}$	20			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	10			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	6			V

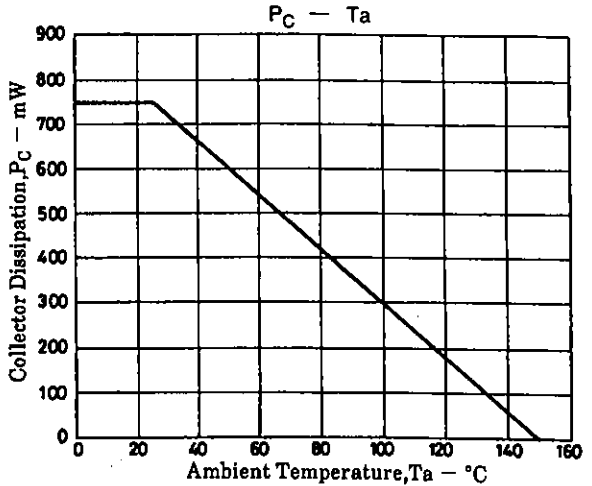
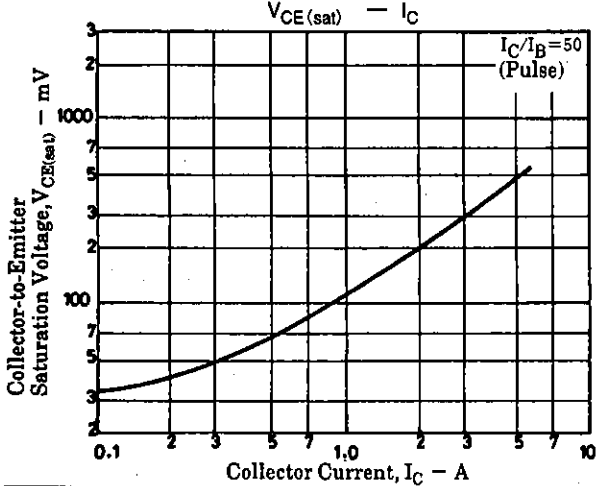
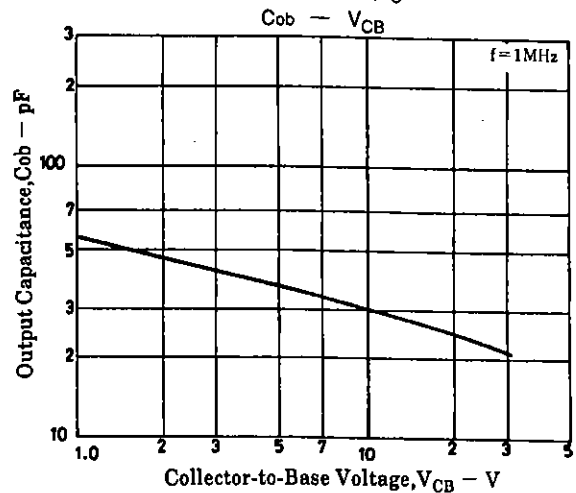
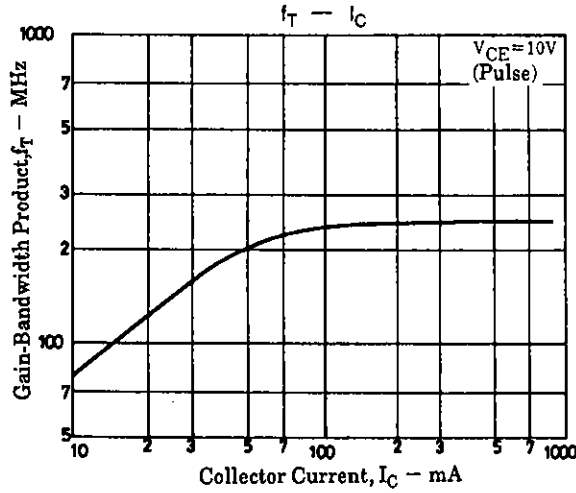
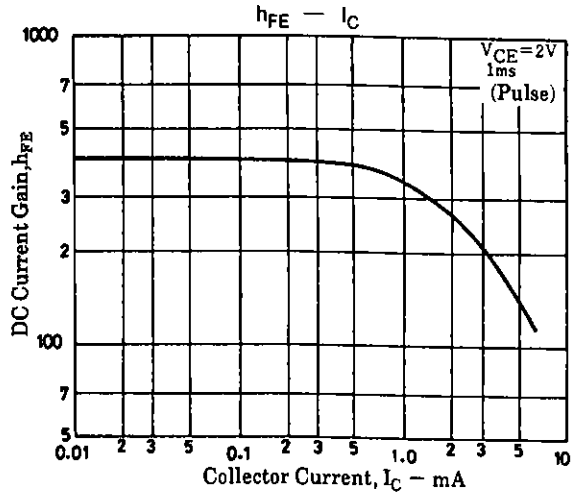
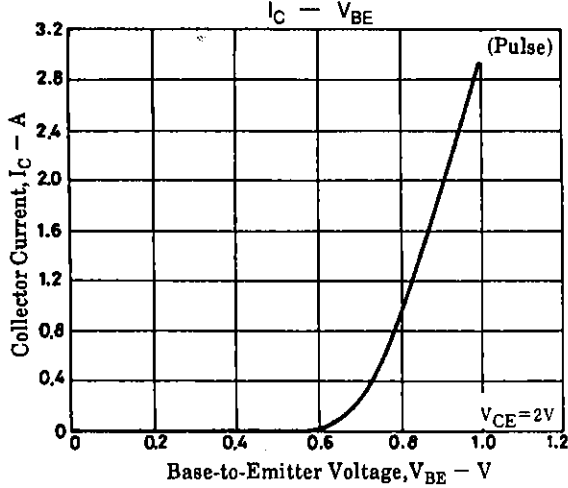
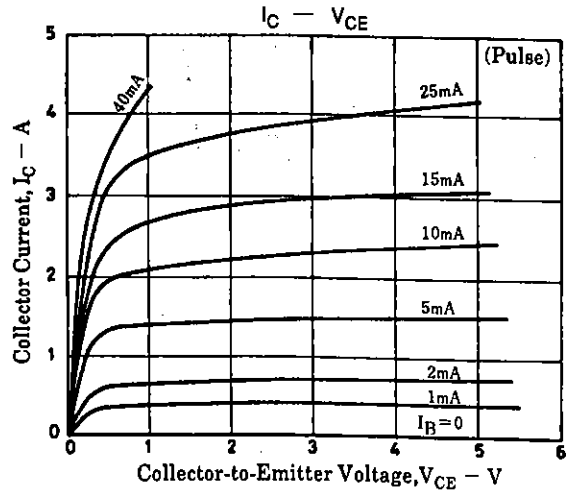
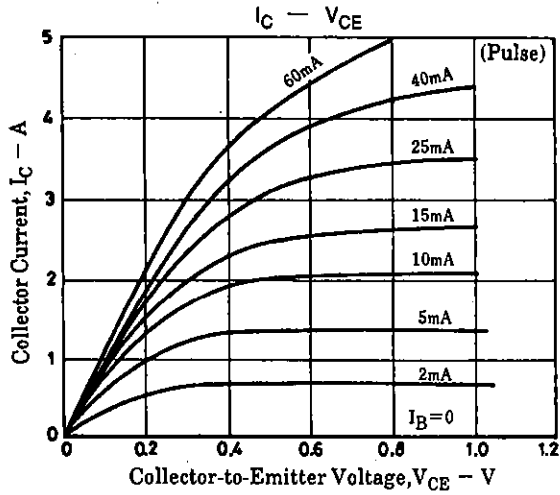
Package Dimensions 2003B (unit : mm)

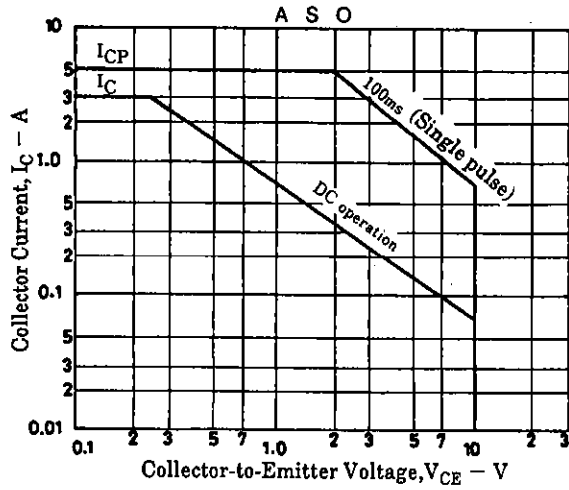


JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

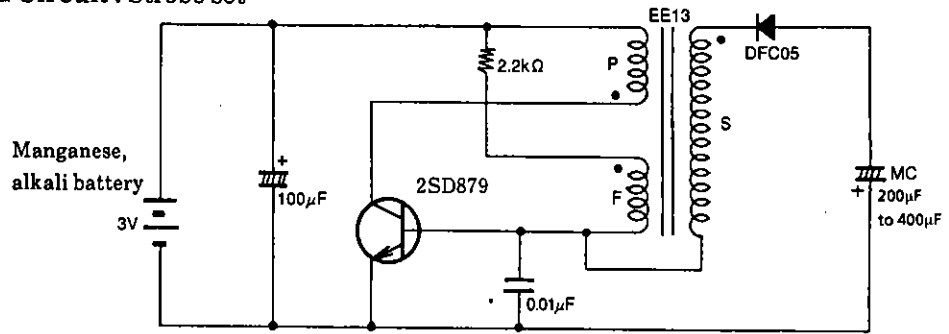
1. Emitter
2. Collector
3. Base

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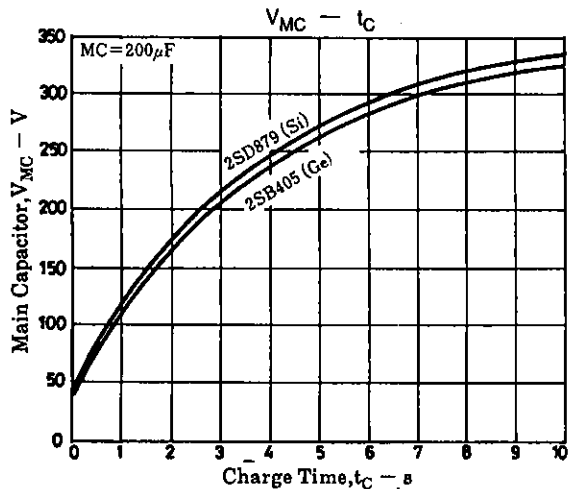
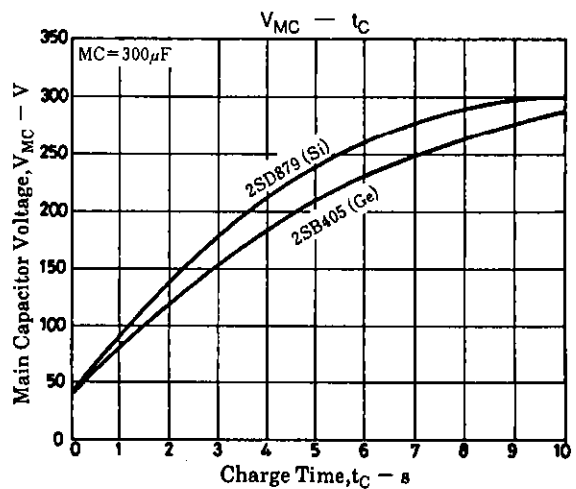
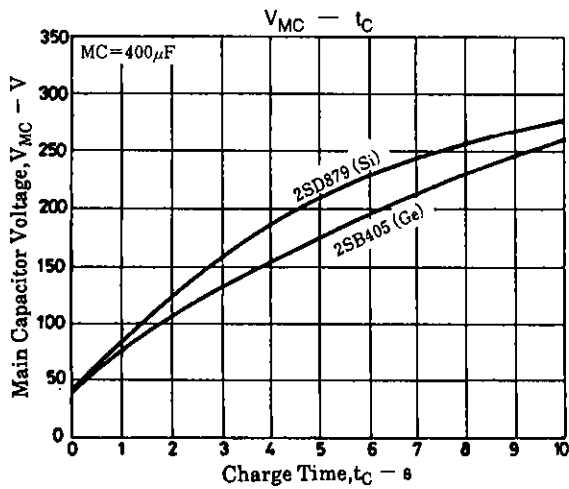


Sample Application Circuit : Strobe set



Core : EE13
(Kijima Wireless)

Number of turns specified for transformer P : $0.55 \phi \times 10 \frac{3}{4} T$, S : $0.07 \phi \times 1350 T$
F : $0.23 \phi \times 12 \frac{3}{4} T$



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